

9097250 TOSHIBA (DISCRETE/OPTO)

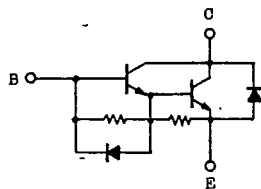
90D 16279 DT-33-35



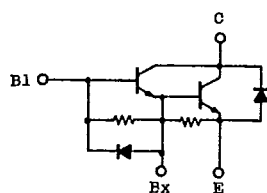
SEMICONDUCTOR

TECHNICAL DATA

MG200H1AL2
MG200H1FL1A

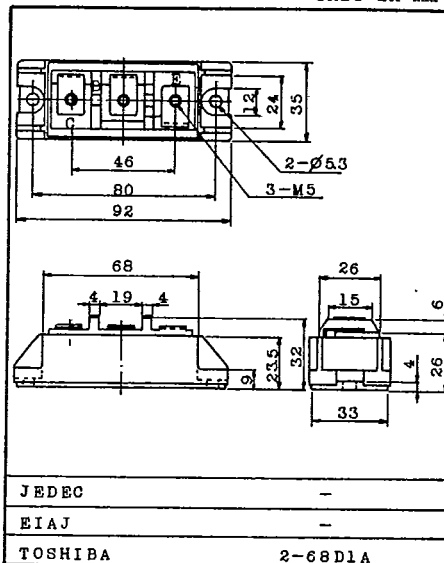


MG200H1AL2



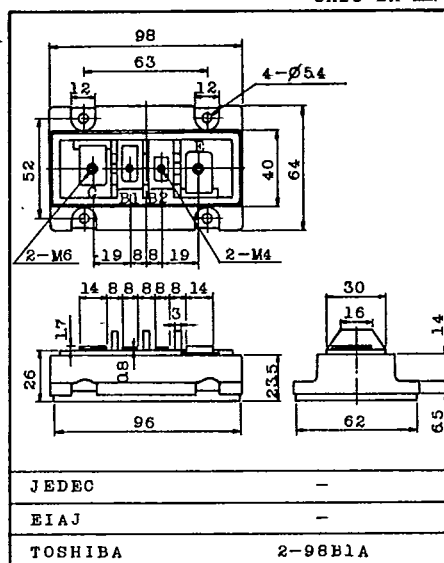
MG200H1FL1

Unit in mm



Weight : 210g

Unit in mm



Weight : 420g

TOSHIBA CORPORATION

GT1A2A

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MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB10}	600	V
Collector-Emitter Voltage		V_{CEO}	600	V
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	550	V
Emitter-Base Voltage		V_{EB10}	6	V
Collector Current	DC	I_C	200	A
	1ms	I_C	400	
	DC	$-I_C$	200	
Base Current		I_{B1}	8	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)		P_C	800	W
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-40~125	$^\circ\text{C}$
Isolation Voltage		V_{isol}	2500 (AC 1 Minute)	V
Screw Torque (Terminal M4/M6/Mounting)		-	20/30/30	kg·cm

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CB10}	$V_{CB1}=600\text{V}$, $I_E=0$	-	-	2.0	mA
Emitter Cut-off Current		I_{EB10}	$V_{EB1}=6\text{V}$, $I_C=0$	-	-	400	mA
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	$I_C=0.5\text{A}$, $L=40\text{mH}$	550	-	-	V
DC Current Gain		h_{FE}	$V_{CE}=5\text{V}$, $I_C=200\text{A}$	80	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=200\text{A}$, $I_{B1}=6\text{A}$	-	-	2.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$		-	-	2.7	V
Emitter-Collector Voltage		V_{ECO}	$I_E=200\text{A}$, $I_{B1}=0$	-	-	1.5	V
Reverse Recovery Time		t_{rr}	$-I_C=200\text{A}$, $V_{EB1}=3\text{V}$ $V_{CE}=300\text{V}$	-	-	2.0	μs
Collector Output Capacitance		C_{ob1}	$V_{CB1}=50\text{V}$, $I_E=0$ $f=1\text{MHz}$	-	1670	-	pF
Switching Time	Turn-on Time	t_{on}		-	-	2.0	μs
	Storage Time	t_{stg}		-	-	12	
	Fall Time	t_f		-	-	4.0	
Thermal Resistance (Junction to Case)		$R_{th(j-c)}$	Transistor	-	-	0.156	$^\circ\text{C/W}$
			Diode	-	-	0.65	

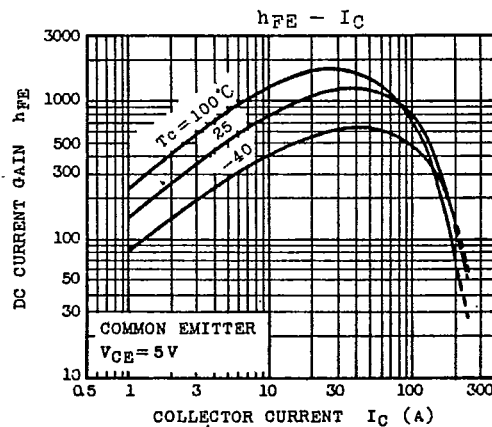
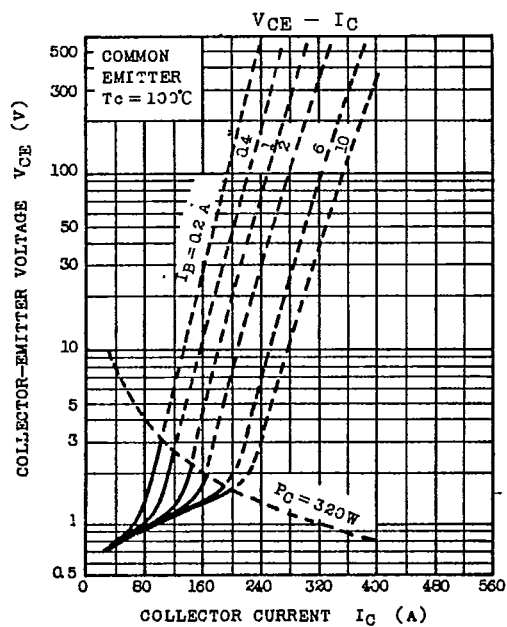
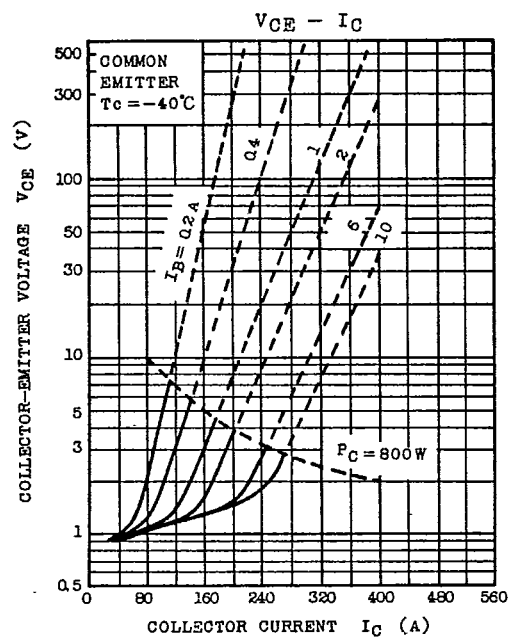
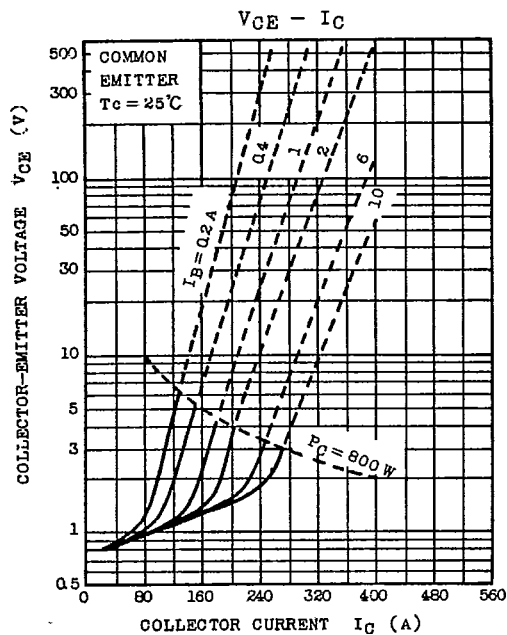
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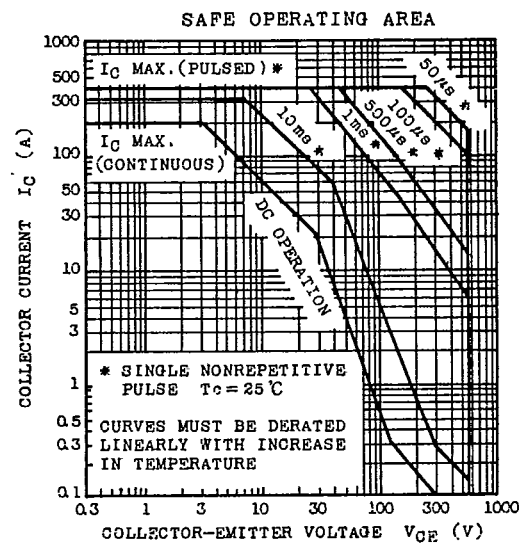
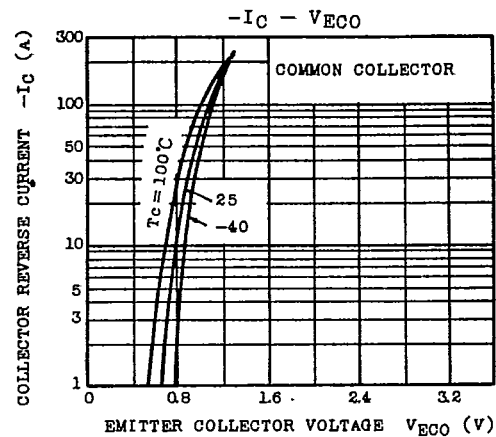
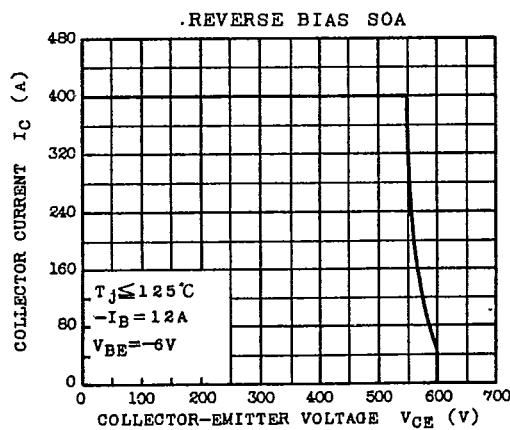
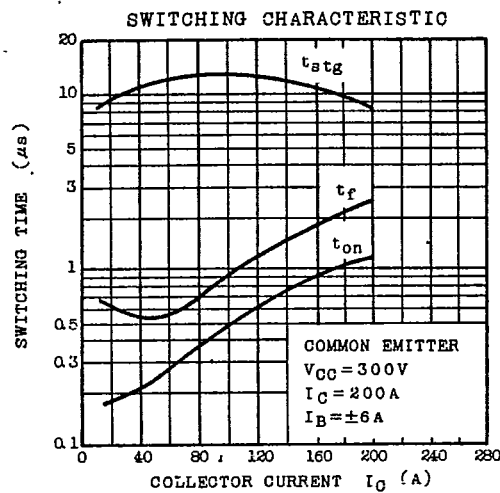
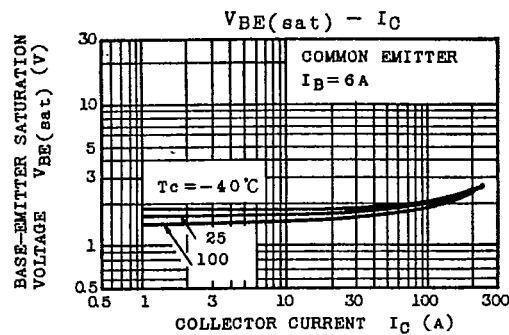
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GT1A2



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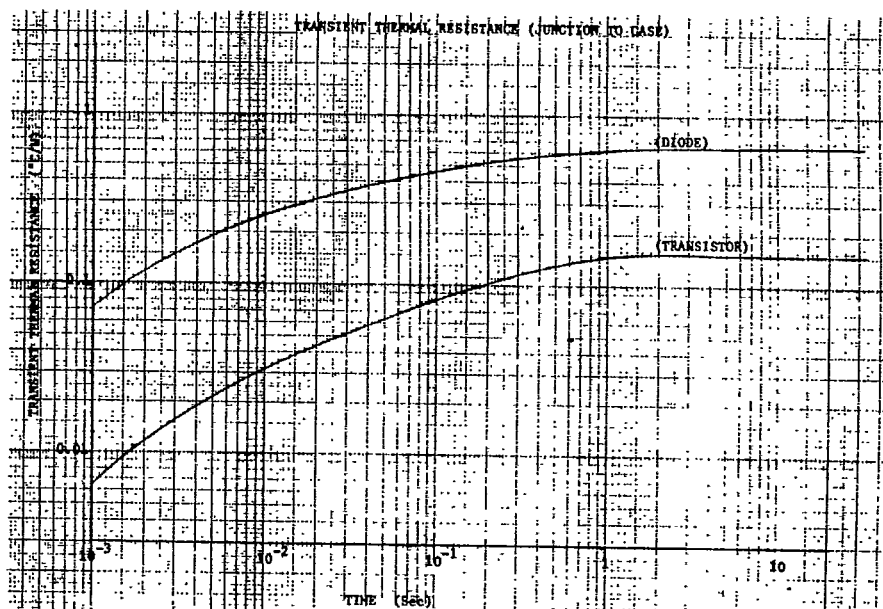
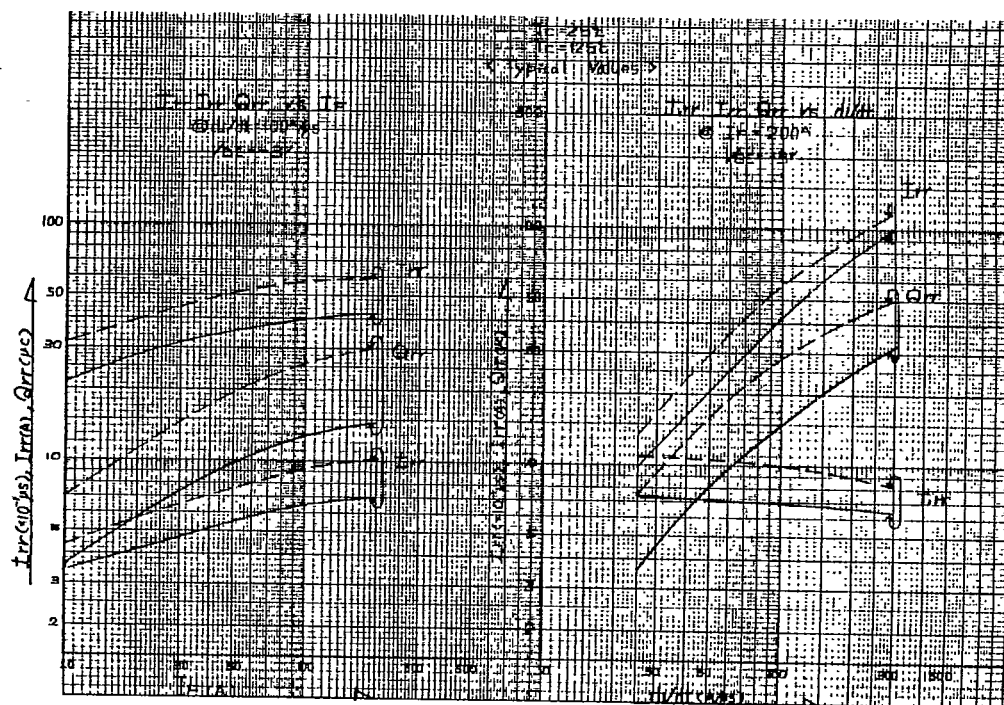
GT1A2



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